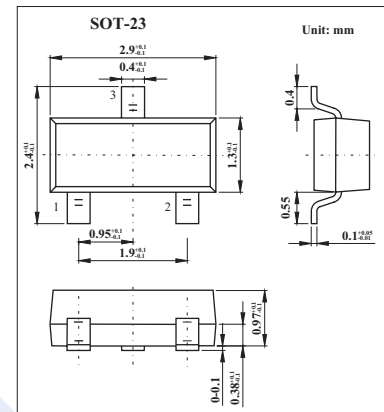
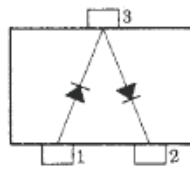


Schottky Barrier Diode

1SS358

■ Features

- Small interterminal capacitance
- Low forward voltage and excellent detection efficiency
- High breakdown voltage



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
peak reverse voltage	V _R	55	V
Forward current	I _F	10	mA
Power dissipation	P	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature range	T _{stg}	-55 to + 125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	I _F = 1 mA			0.35	V
Reverse voltage	V _R	I _R = 100 μ A	55			V
Forward Current	I _F	V _F = 1V	10			mA
Reverse current	I _R	V _R = 40V			50	μ A
Interterminal I capacitance	C	V _R = 0, f = 1.0 MHz		0.45		pF

■ Marking

Marking	DH